

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	$I_D$
30 V	42 mΩ	4.2 A

**SOT-23** 

### **Features**

- $R_{DS(ON)}$ =48m  $\Omega$  @ $V_{GS}$ =4.5V
- $R_{DS(ON)}$ =42m  $\Omega$  @ $V_{GS}$ =10V
- ESD Protected 2KV HBM
- · Green Device Available

### **Applications**

• Case : SOT-23

• Terminals: Solderable per MIL-STD-750,

Method 2026

Absolute Maximum Ratings TA=25°C unless otherwise noted							
Symbol	Parameter	Rating	Units				
V <sub>DS</sub>	Drain-Source Voltage	30	V				
$V_{GS}$	Gate-Source Voltage	±12	V				
I <sub>D</sub>	Drain Current - Continuous	4.2	Α				
I <sub>DM</sub>	Drain Current - Pulsed	16.8	Α				
P <sub>D</sub>	Power Dissipation (T <sub>a</sub> =25°C)	1.25	W				
T <sub>J</sub>	Operating Junction Temperature Range	-50 to 150	°C				
T <sub>STG</sub>	Storage Temperature Range	-50 to 150	°C				
Marking Code		A22					

Thermal Characteristics						
Symbol	pol Parameter Typ. Max		Max	Unit		
$R_{ hetaJA}$	Thermal Resistance Junction to Ambient		100	°C/W		





### Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ =0V , $I_D$ =250uA	30			V
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =30V , $V_{GS}$ =0V			1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ =±12V , $V_{DS}$ =0V			±10	uA

#### **On Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
		$V_{GS}$ =2.5V , $I_D$ =2.8A		-	55	
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}$ =4.5V , $I_D$ =3.5A		-	48	mΩ
		V <sub>GS</sub> =10V , I <sub>D</sub> =4.2A			42	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_{D}=250uA$	0.5	0.8	1.3	V

#### Dynamic and switching Characteristics (NOTE 4)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$Q_g$	Total Gate Charge	\\ -45\\ \\ -45\\ \\ -45\\ \\ -420		5.1		
$Q_{gs}$	Gate-Source Charge	V <sub>DS</sub> =15V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =4.2A (NOTE 1 \ 2)		0.8		nC
$Q_{gd}$	Gate-Drain Charge	(NOTE 1 · 2)		1.4		
$T_{d(on)}$	Turn-On Delay Time	V 45V V 40V B 00		2.8		
T <sub>r</sub>	Rise Time	$V_{DD}$ =15V , $V_{GS}$ =10V , $R_{G}$ =3 $\Omega$ ,		22		no
$T_{d(off)}$	Turn-Off Delay Time	I <sub>D</sub> =1A (NOTE 1 \ 2)		21		ns
$T_f$	Fall Time	(10121 2)		16		
$C_{iss}$	Input Capacitance			421		
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , F=1MHz		43		pF
$C_{rss}$	Reverse Transfer Capacitance			35		

## **Drain-Source Diode Characteristics and Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	$V_G=V_D=0V$ , Force Current		-	1.5	Α
$V_{SD}$	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =1A			1.2	V

### NOTES:

- 1. Pulse width  $\leq$  300us , duty cycle  $\leq$  2%.
- $2. \ Essentially \ independent \ of \ operating \ temperature \ typical \ characteristics.$
- 3. The maximum current rating is package limited.
- ${\bf 4.} \ {\bf Guaranteed} \ {\bf by} \ {\bf design}, \ {\bf not} \ {\bf subject} \ {\bf to} \ {\bf production} \ {\bf testing}.$





#### **Characteristics Curves**

FIG. 1-On-Region Characteristics

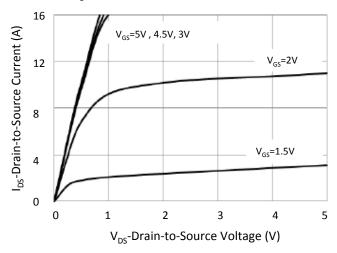


FIG. 2-Transfer Characteristics

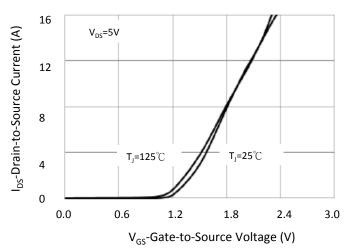


FIG. 3-On-Resistance vs Drain Current

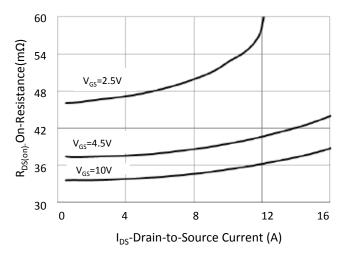


FIG. 4-On-Resistance vs Junction Temperature

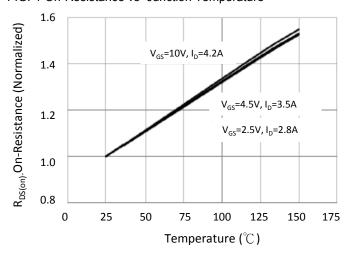


FIG. 5-On-Resistance vs Variation with V<sub>GS</sub>

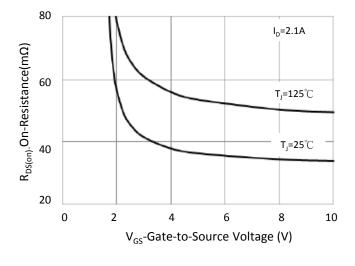
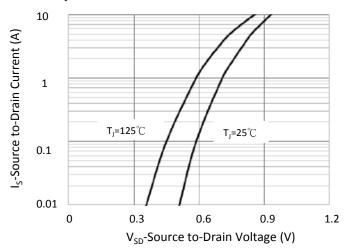


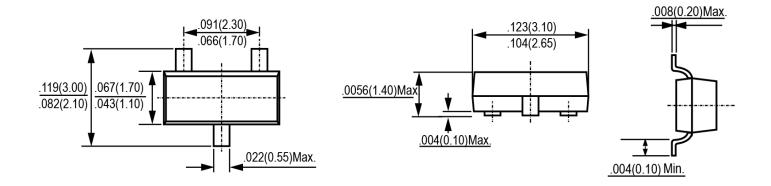
FIG. 6-Body Diode Characteristics





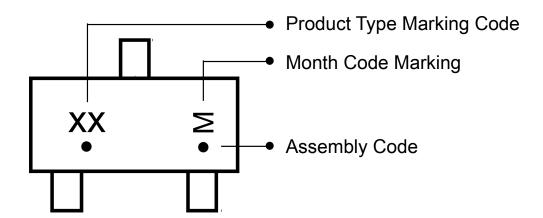


#### **Package Outline Dimensions**



**SOT-23** Dimensions in inches and (millimeters)

## **Marking Information**







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